PATENT APPLICATION

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		STAT	EMENT	Peter J Fricke et	I GROUP	_	
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	1Δ	6,521,958	Feb 2003	Forbes et al	The state of the s	_	
	+	6,297,989	Oct 2001	Cloud et al		-	
	1C	6,288,437	Sep 2001	Forbes et al		_	
. <u>-</u>	1D	6,118,138	Sep 2000	Farnworth et al		_	
	1E	5,847,441	Dec 1998	Cutter et al		_	
	1F	6,483,736	Nov 2002	Johnson et al		_	
	1G	6,661,691	Dec 2003	Fricke et al		_	
	1H	6,051,851	Apr 2000	Ohmi et al			
	11	6,153,468	Nov 2000	Forbes et al			
	1J	5,625,220	Apr 1997	Liu et al		_	
	1K	5,581,501	Dec 1996	Sansbury et al			
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	1M 1N 10 1P	OTHER REF Chan et al, "N Electron Device Thomas H Lec	ERENCES (including Multiple Layers of CN to Letters, V.22 (2), te, "A Vertical Leap for the control of the cont	OR APPLICANT OR AUTHOR OR AUT	Pages/Columns/Lines Where Relevant Passages/Figures Appear Pertinent Pages, etc.) ing Recrystallized Silicon Film", IEEE	ransla	

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	1	2002/0083390	Jun 27, 2002	+	et al				
		2002/0075719	Jun 20, 2002	┪	nson et al				
		2002/0058408	May 16, 2002	+	ydan et al				
		2001/0055838	Dec 27, 2001		lker et al				
		2001/0036750	Nov 01, 2001	+	lens et al	-			
	-	2001/0011776	Aug 09, 2001	+-	rashi et al				
		6,372,633	Apr 16, 2002	+	ydan et al				
		6,380,003	Apr 30, 2002	+	nes et al				
	\vdash	6,351,406	Feb 26, 2002	Joh	nson et al		······································		
	-	6,251,710	Jun 26, 2001	Rac	lens et al				
	2K	6,185,122	Feb 06, 2001	Joh	nson et al				
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		OTHER REF	ERENCES (includin	ıg Au	thor, Title, Date, Pe	ertinen	t Pages, etc.)		
	20	Chenming Hu, Devices Meeti	"Interconnect devic ng, IEDM 92, April	es for 1992,	field programmable ç pp 591-594	gate ar	ray", IEEE Int'I	Electron	_
- .	2F	Jonathan Gree 1993, pp 104		eld Pr	ogrammable Gate Arr	rays", I	Proc. IEEE, Vol	81(7), July	
	25	Kulkarni et al, Electrochem S	"Patterning of Subnoc., V. 135 (12), Do	nicron ec. 19	Metal Features and F 88, pp 3094-3098	Pillars i	n Multilevel Me	tallization", J.	
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	ЗА	6,111,302	Aug 29, 2000	Zhang et al		
	ЗВ	6,034,882	Mar 07, 2000	Johnson et al		_
	3C	5,821,558	Oct 13, 1998	Han et al		
	3D	5,751,012	May 12, 1998	Wolstenholme et al		_
	3E	5,335,219	Aug 02, 1994	Ovshinsky et al		
	3F	4,599,705	Jul 08, 1986	Holmberg et al		
	3G	4,499,557	Feb 12, 1985	Holmberg et al	,	
	зн	3,641,516	Feb 08, 1972	Castrucci et al		
	31	3,530,441	Sep 22, 1970	Ovshinsky		
	31	3,271,591	Sep 06, 1966	Ovshinsky		
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